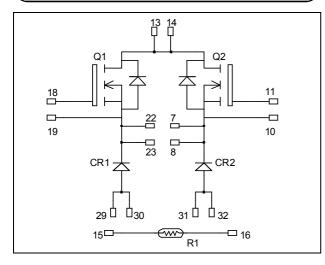
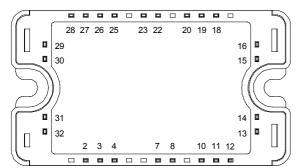


Dual buck chopper Super Junction MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		600	V
I _D	Continuous Drain Current $\frac{T_c = 25^{\circ}C}{T_c = 80^{\circ}C}$		72	
ID			54	А
I _{DM}	Pulsed Drain current		288	
V _{GS}	Gate - Source Voltage		±20	V
R _{DSon}	Drain - Source ON Resistance		35	mΩ
P _D	Maximum Power Dissipation $T_c = 25^{\circ}C$		416	W
I _{AR}	Avalanche current (repetitive and non repetitive)		20	А
E _{AR}	Repetitive Avalanche Energy		1	mJ
E _{AS}	Single Pulse Avalanche Energy		1800	111J

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

APTC60DSKM35T3G

 $V_{DSS} = 600V$ $R_{DSon} = 35m\Omega \text{ max} @ Tj = 25^{\circ}C$ $I_D = 72A @ Tc = 25^{\circ}C$

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- - Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate chargeAvalanche energy rated
 - Avalancie energy rate
 Very rugged
 - Very rugged
- Kelvin source for easy driveVery low stray inductance
- Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability
- RoHS Compliant



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 25^{\circ}C$			40	μΑ
		$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 125^{\circ}C$	2		375	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 72A$			35	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5.4 \text{mA}$	2.1	3	3.9	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0V$			±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		14		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		5.13		nF
C _{rss}	Reverse Transfer Capacitance	f=1MHz		0.42		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		518		
Q _{gs}	Gate – Source Charge	$V_{Bus} = 300V$		58		nC
Q_{gd}	Gate – Drain Charge	$I_D = 72A$		222		
T _{d(on)}	Turn-on Delay Time	Inductive Switching @ 125°C		21		
Tr	Rise Time	$V_{GS} = 15V$		30		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_D = 72A$		283		ns
T_{f}	Fall Time	$R_G = 2.5\Omega$		84		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1340		
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		1960		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		2192		
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		2412		μJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_{i} = 25^{\circ}C$ $T_{i} = 125^{\circ}C$			350 600	μΑ
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		80		А
V	V_F Diode Forward Voltage $I_F = 80A$ $V_{GE} = 0V$	$I_F = 80A$	$T_i = 25^{\circ}C$		1.45		V
V F		$T_{i} = 125^{\circ}C$		1.35		v	
t	Reverse Recovery Time $I_{-} = 80 \text{ A}$	$T_j = 25^{\circ}C$		95		ns	
t _{rr}	Reverse Recovery Time	$I_{\rm F} = 80A$ $V_{\rm R} = 300V$	$T_j = 125^{\circ}C$		115		115
Q _{rr}	Reverse Recovery Charge	$v_R = 300 v$ di/dt =4500A/µs	$T_j = 25^{\circ}C$		5.2		μC
Qrr			$T_j = 125^{\circ}C$		8		μυ



Thermal and package characteristics

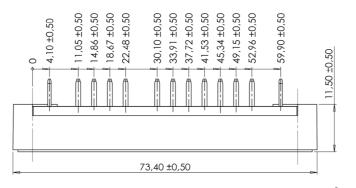
Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance Transiston Diode	Transistor			0.3	°C/W	
R _{thJC}		Diode			0.8	C/ W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				110	g	

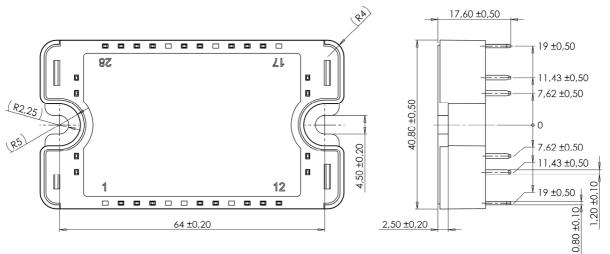
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP3 Package outline (dimensions in mm)

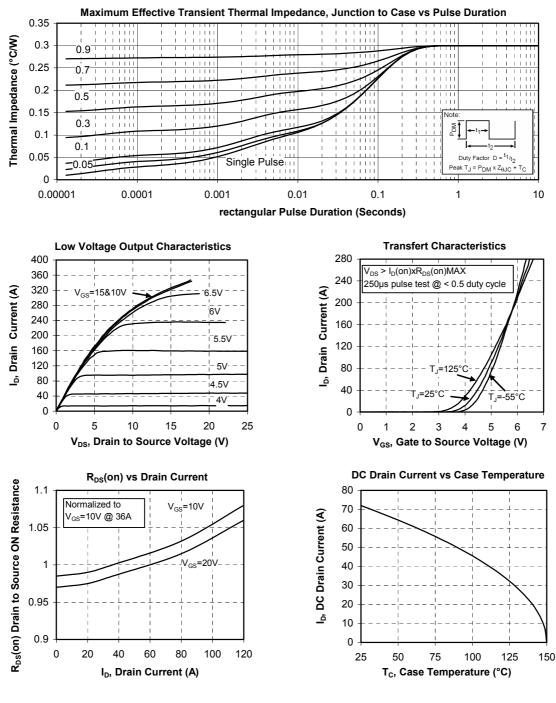




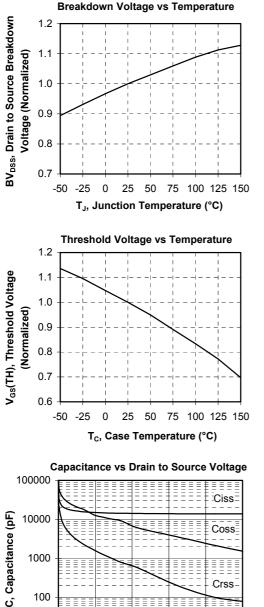
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com



Typical Performance Curve

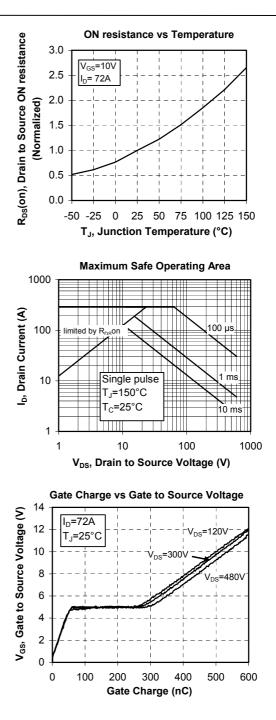




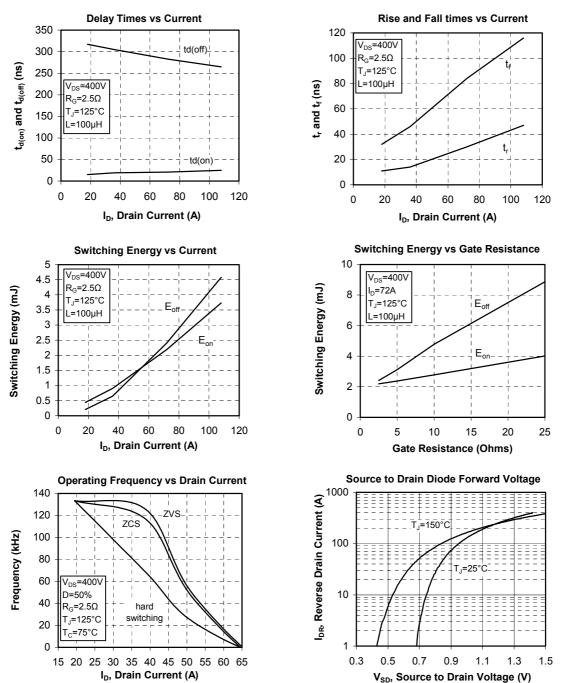


100 10 0 10 20 30 40 50 V_{DS} , Drain to Source Voltage (V)

APTC60DSKM35T3G







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